



TO-251-3L Plastic-Encapsulate Transistors

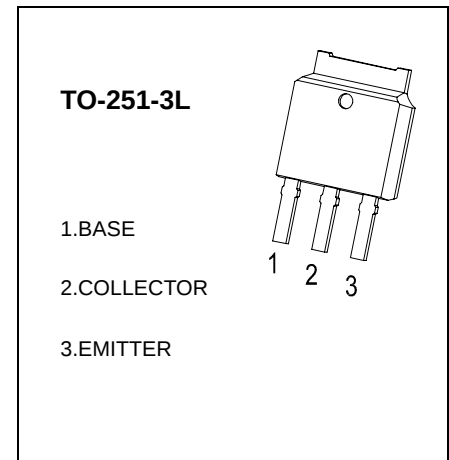
MJD2955 TRANSISTOR (PNP)

FEATURES

- Designed for General Purpose Amplifier and Low Speed Switching Applications
- Electrically Simiar to MJD3055
- DC Current Gain Specified to10 Amperes

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-70	V
V _{CEO}	Collector-Emitter Voltage	-60	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-10	A
P _C	Collector Power Dissipation	1.25	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-1mA, I _E =0	-70			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-200 mA, I _B =0	-60			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-1mA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-70V, I _E =0			-0.02	mA
	I _{CEO}	V _{CB} =-30V, I _B =0			-50	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.5	mA
DC current gain	h _{FE(1)}	V _{CE} =-4V, I _C =-4A	20		100	
	h _{FE(2)}	V _{CE} =-4V, I _C =-10A	5			
Collector-emitter saturation voltage	V _{CE(sat)(1)}	I _C =-4A, I _B =-0.4A			-1.1	V
	V _{CE(sat)(2)}	I _C =-10A, I _B =-3.3A			-8	V
Base-emitter voltage	V _{BE}	V _{CE} =-4V, I _C =-4A			-1.8	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-0.5A, f=500KHz	2			MHz